



**PHOTONICS RESEARCH GROUP**

# Navolchi Update September 2013

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**Physics and Chemistry of Nanostructures Group**



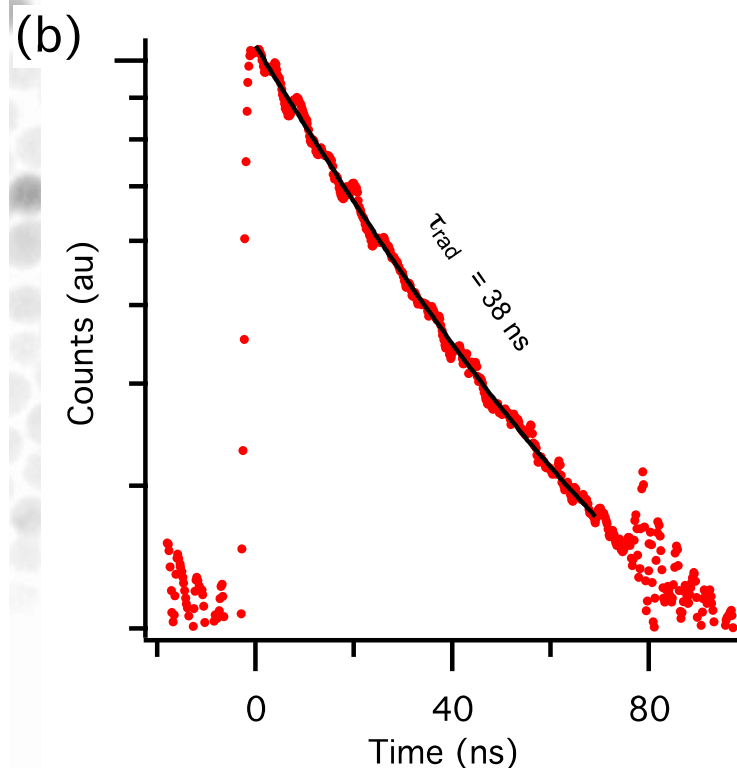
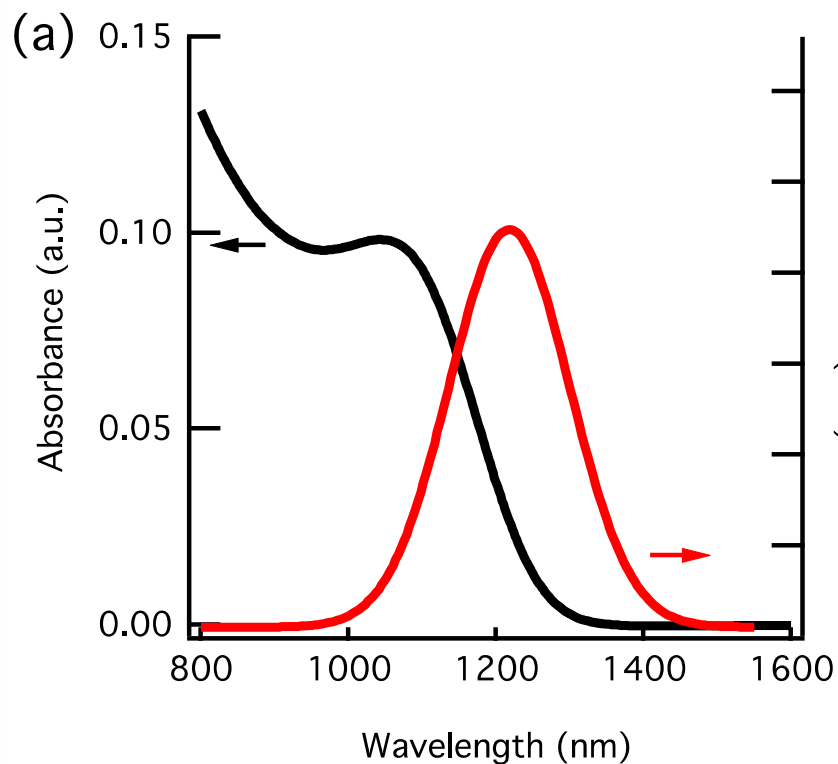
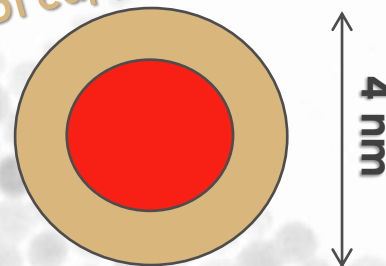
<http://www.nano.UGent.be>

# HgTe linear properties

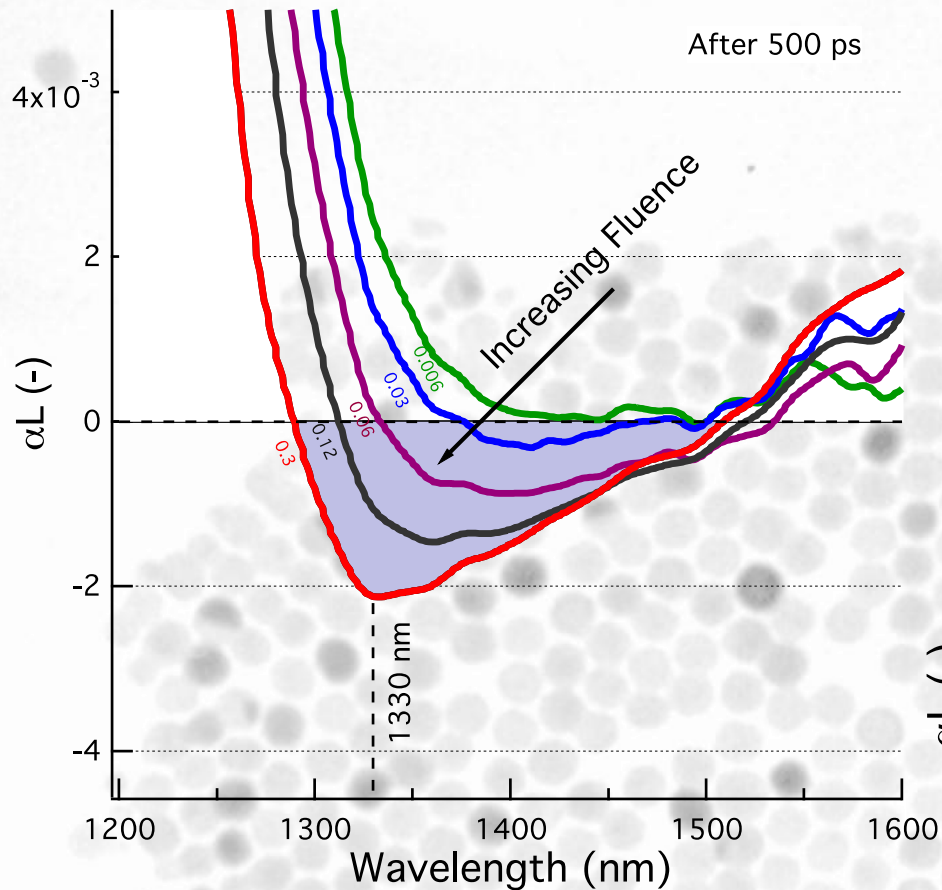
Absorption and emission in the **near-infrared**  
Radiative lifetime: **30-40 ns** , single X decay

Large Stokes shift (up to 100 meV)

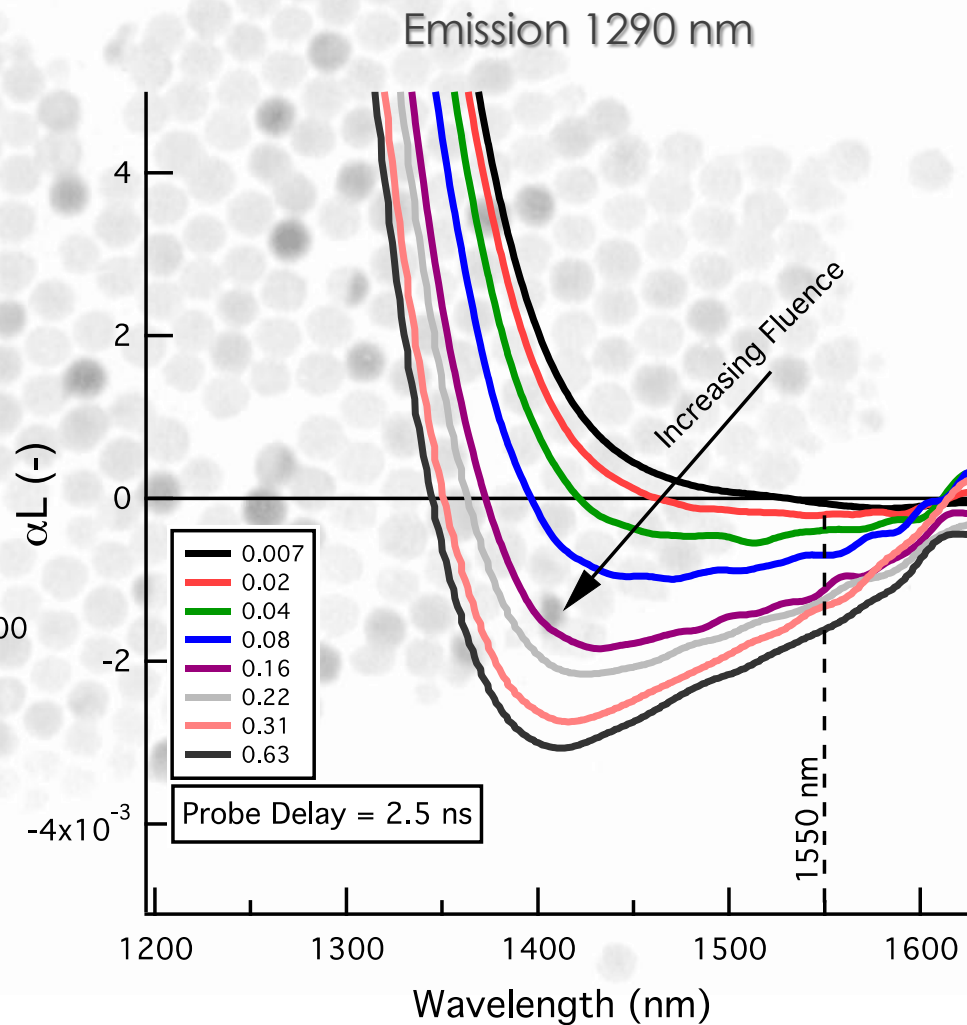
DDT capping



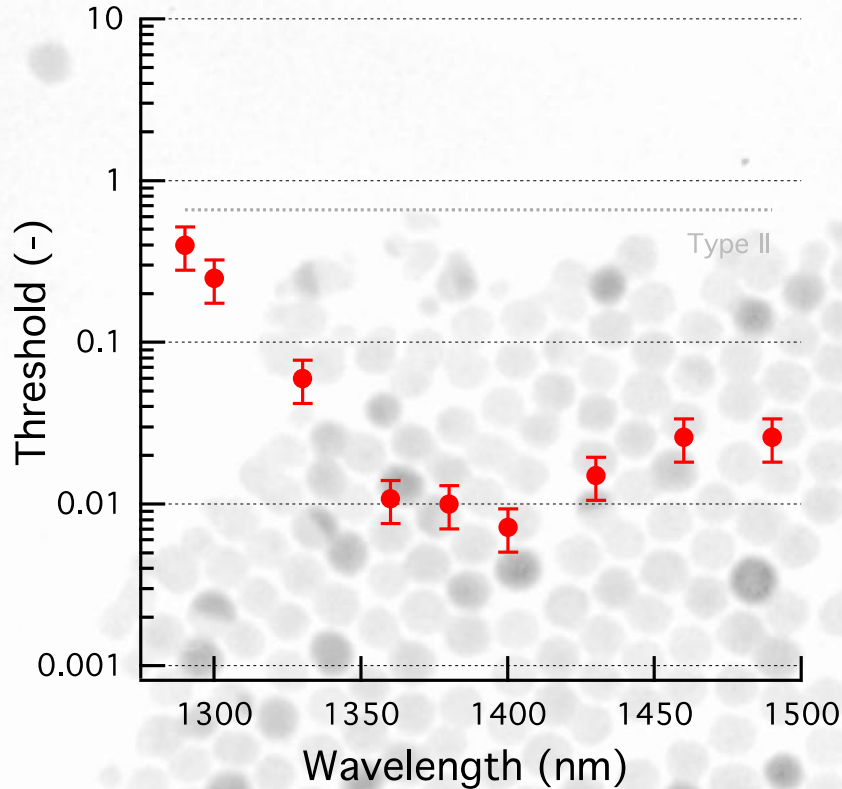
# Non-linear absorption



Emission 1220 nm

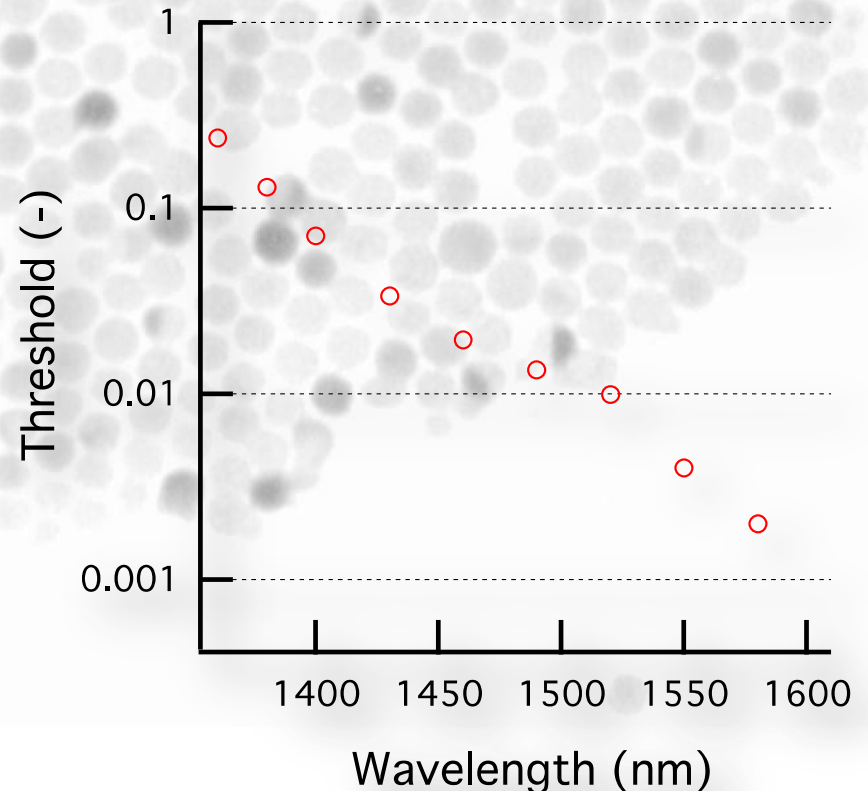


# Thresholdless amplification



“Real threshold is 0, but photo-induced absorption and spectral broadening limits us to 0.01”

“The threshold is far below the single X level and orders of magnitude smaller than the best values obtained so far ( $\langle N \rangle = 2/3$ )”



# Fluence dependence

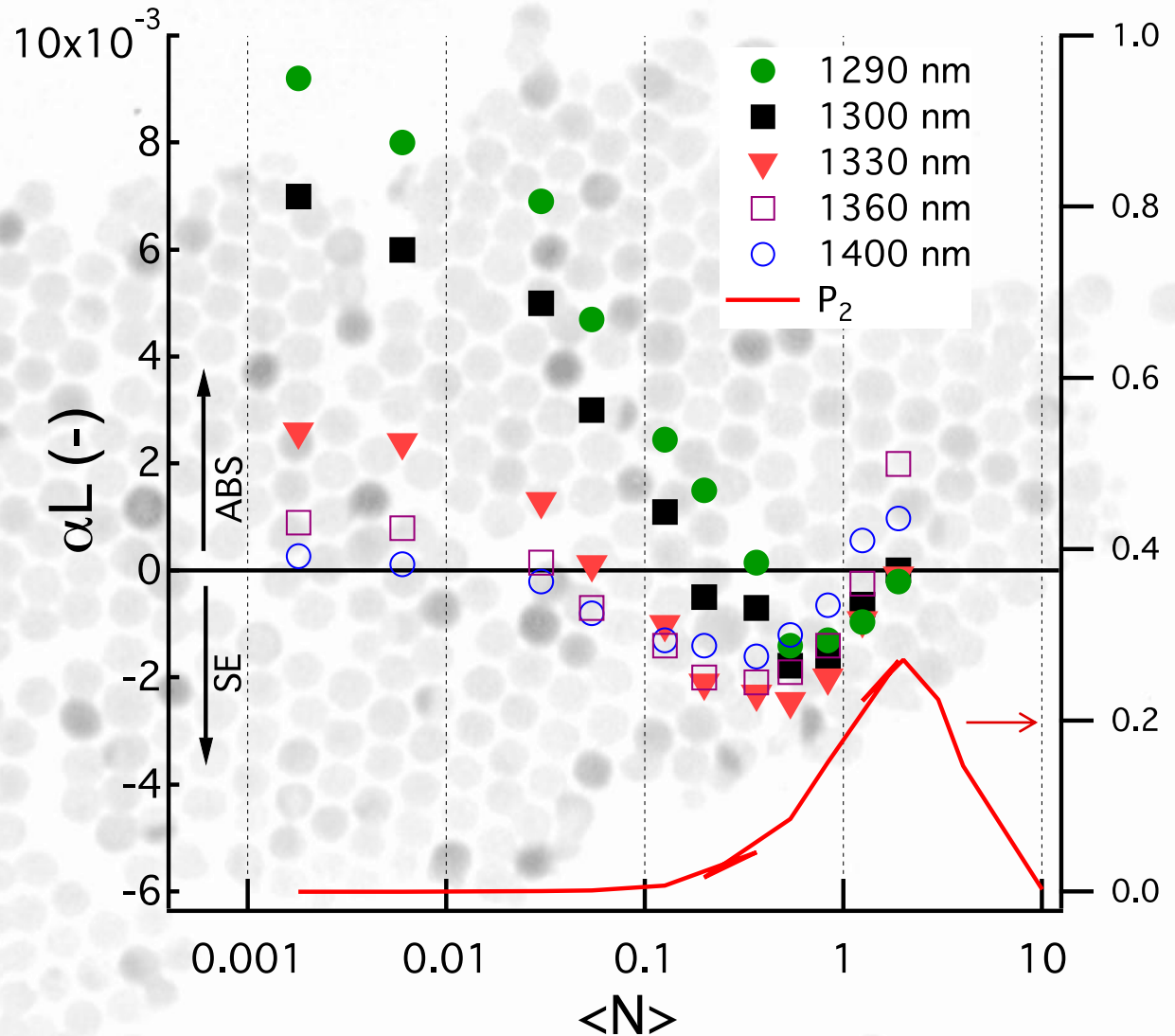
Stimulated emission dominates when increasing the fluence



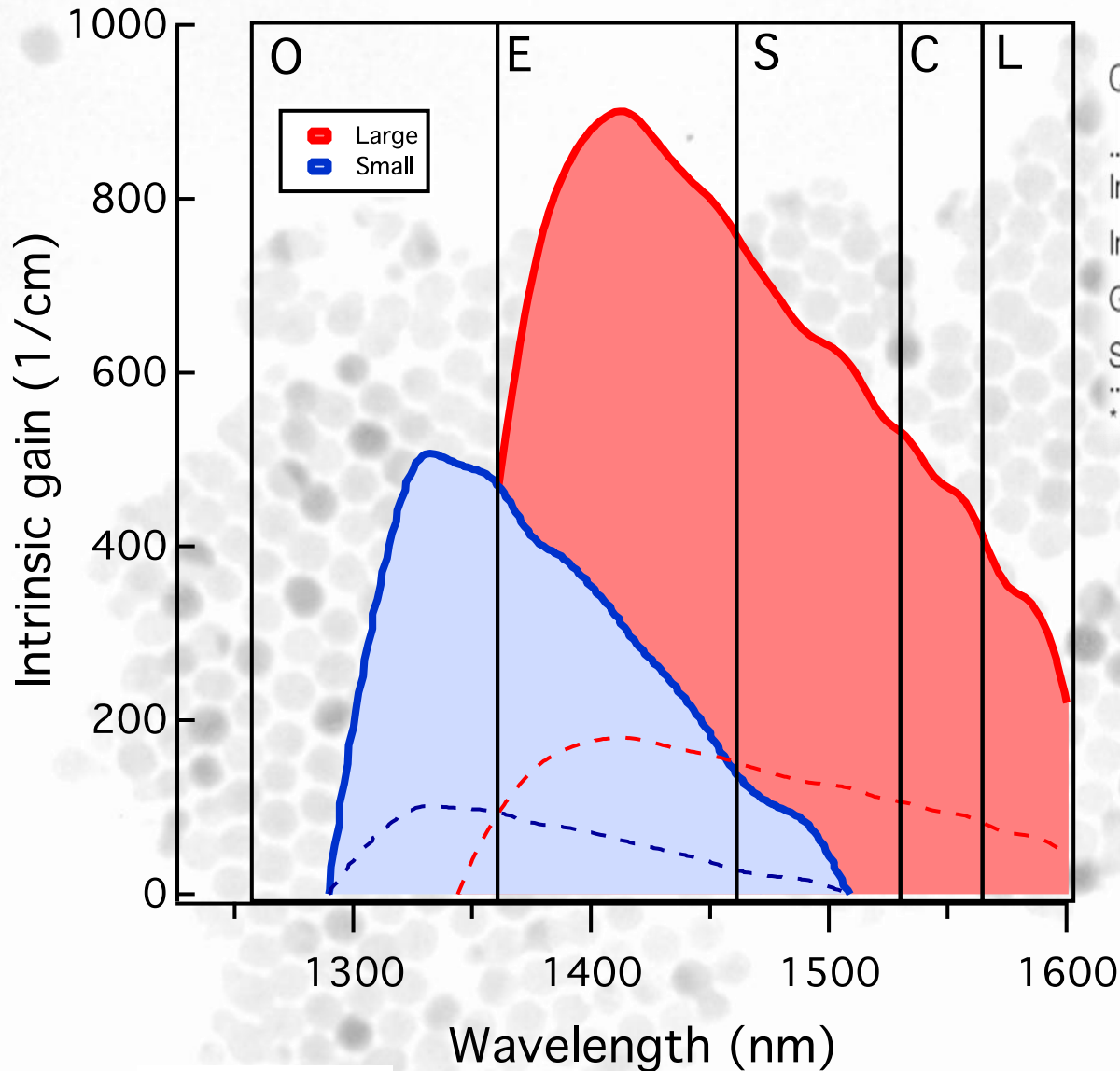
At high fluence, Auger ionization creates hot carriers



Hot carriers give rise to increase of PA



# Intrinsic gain: covering OESCL



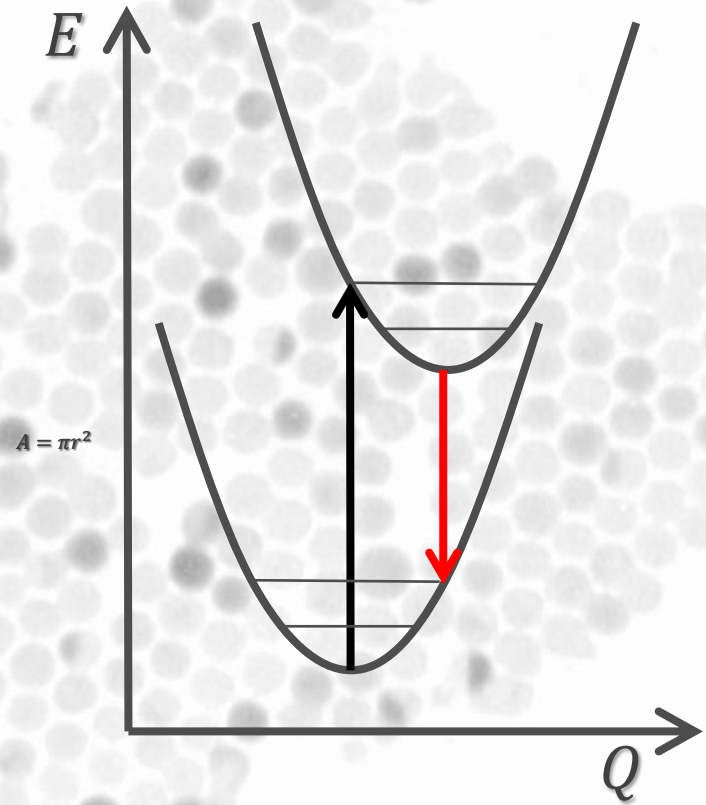
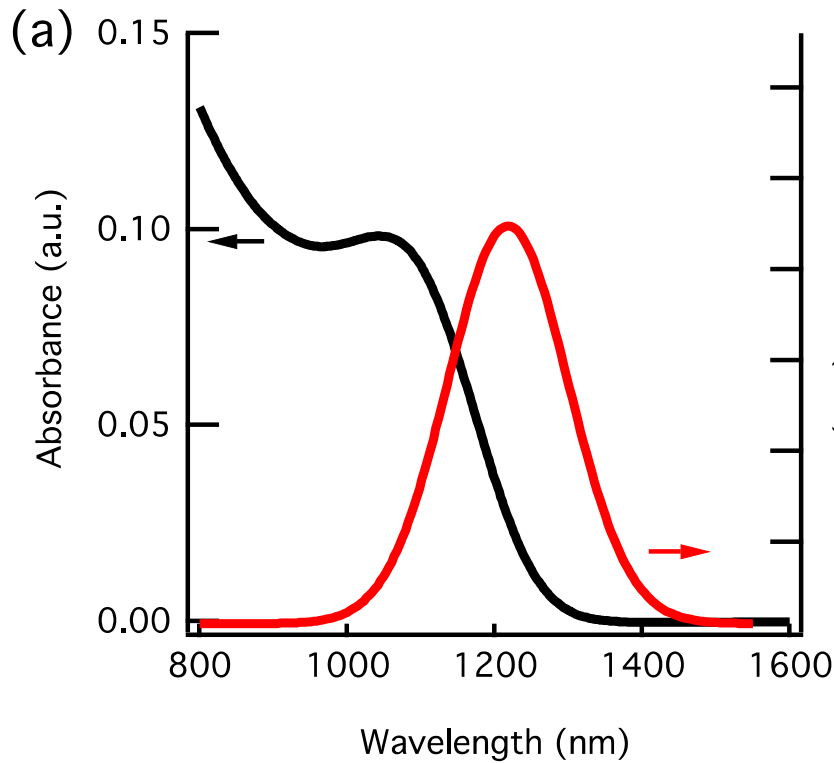
Quantum dot material	Net model gain (cm <sup>-1</sup> )
InAs single layer quantum dot	8.2
InAs 7 stacks quantum dot	70–85
GaAs single layer quantum dot	13*
Si nanocrystals	100

\* Calculated approximately.

Gain comparable to best epitaxial systems !

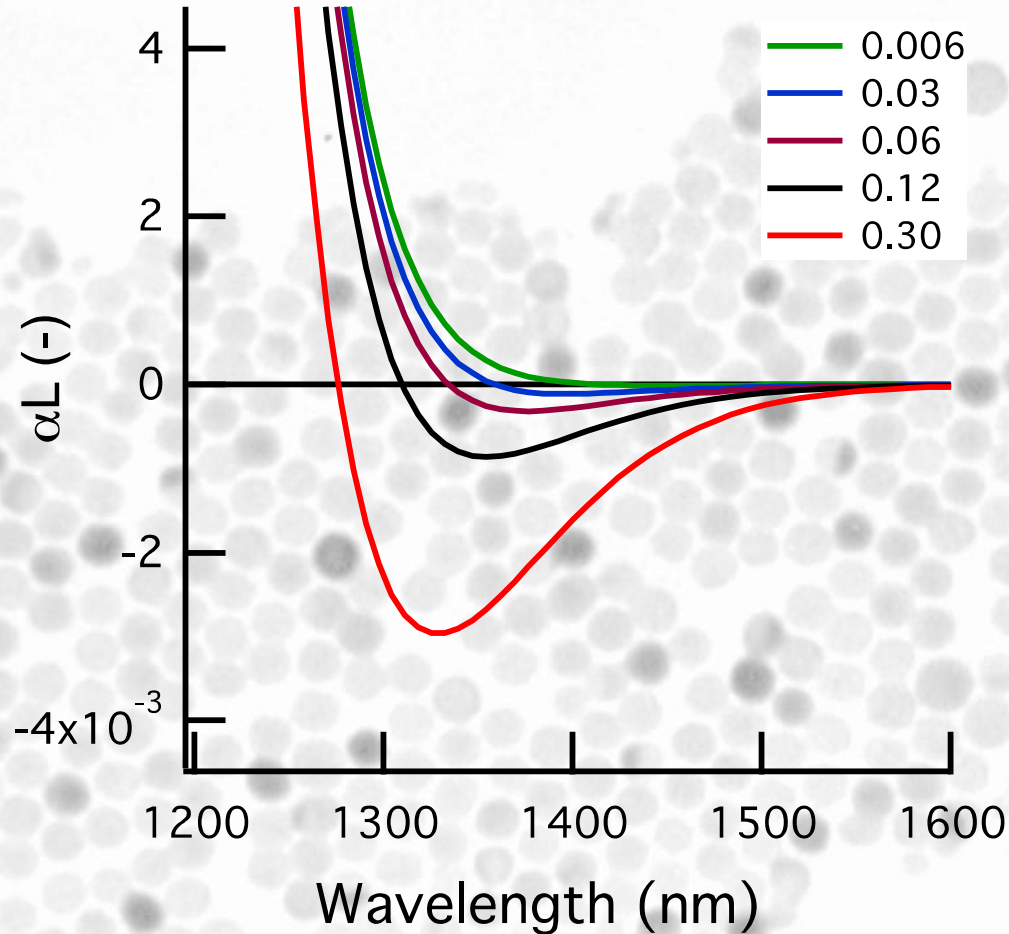
But much more broadband and cheaper materials !

# Gain Mechanism



$$\alpha(\lambda) = \left( N_0 + \frac{3}{8} N_1 \right) \alpha_0(\lambda) - \frac{1}{8} N_1 \alpha_0(\lambda - \lambda_{em})$$

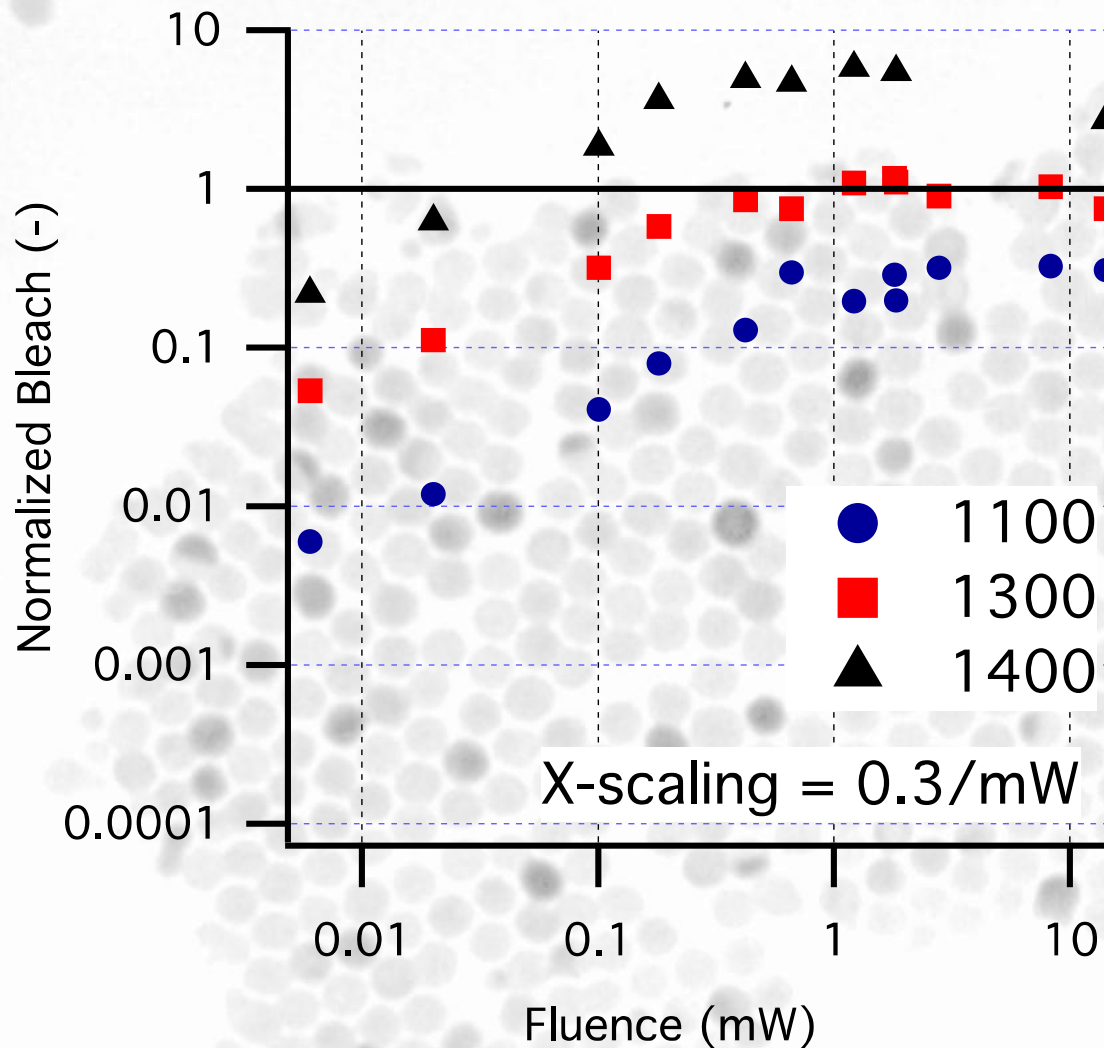
# Gain Mechanism



$$\alpha(\lambda) = \left( N_0 + \frac{3}{8} N_1 \right) \alpha_0(\lambda) - \frac{1}{8} N_1 \alpha_0(\lambda - \lambda_{em})$$



# Normalized spectra



$$\frac{-Da}{a_0} > 1$$

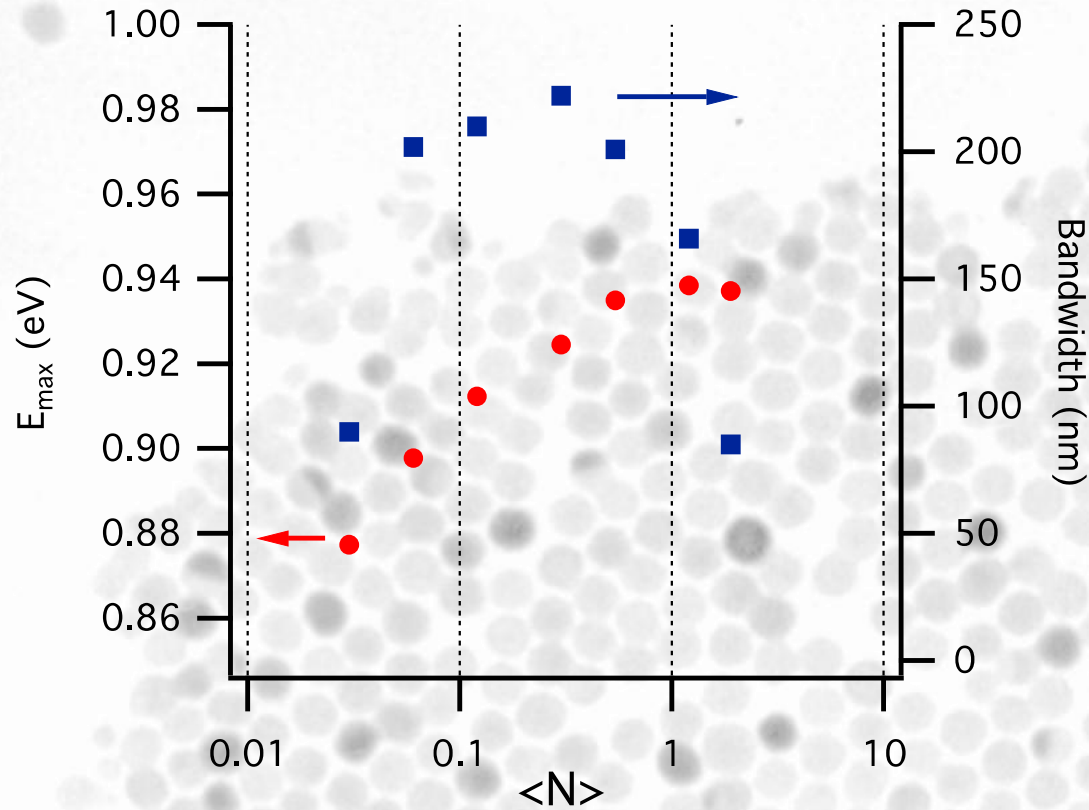
Transparency reached at sub-X level !

Normalized bleach > 1, indicative of red-shifted emission/gain band

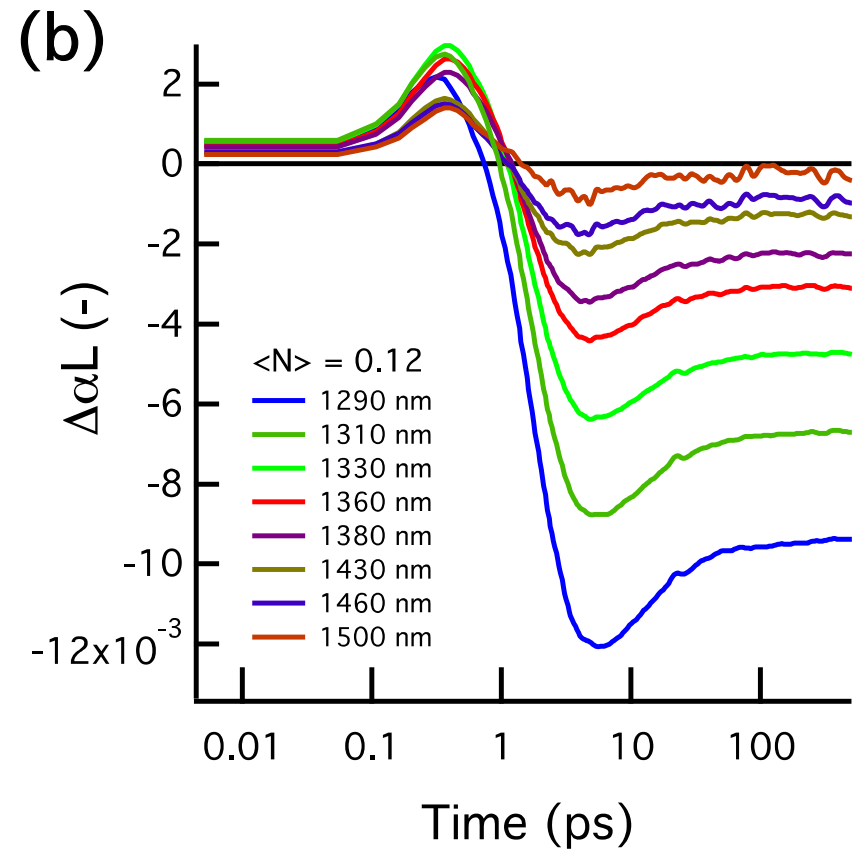
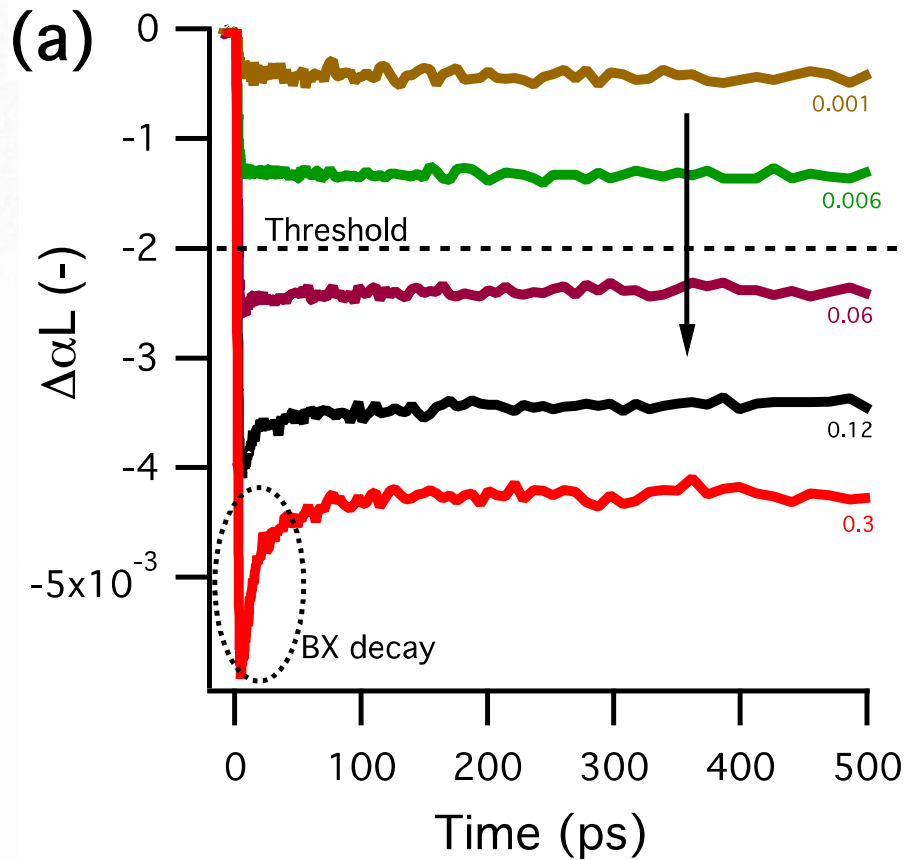


Gain comes from different 2-level system than absorption !

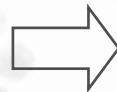
# Gain maximum and bandwidth



# Kinetics

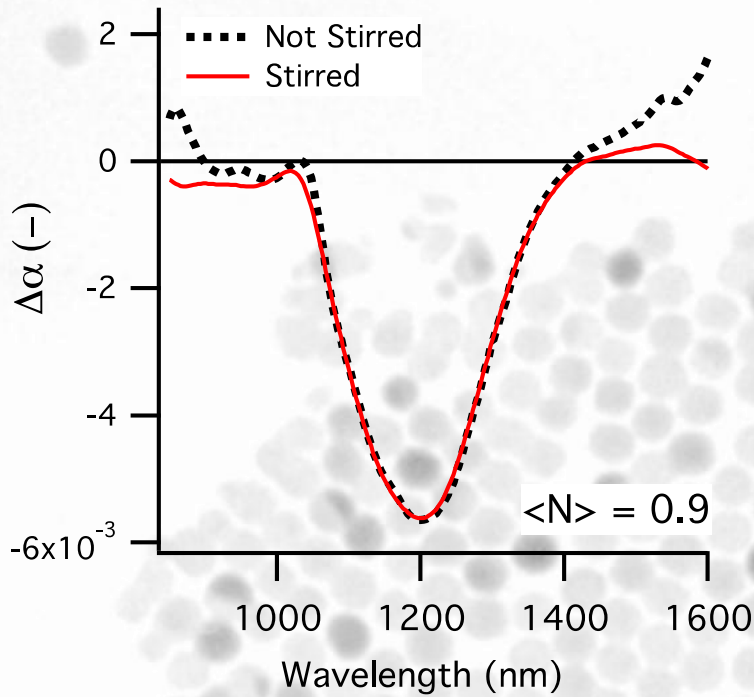


**Bleach lives for >3 ns !**

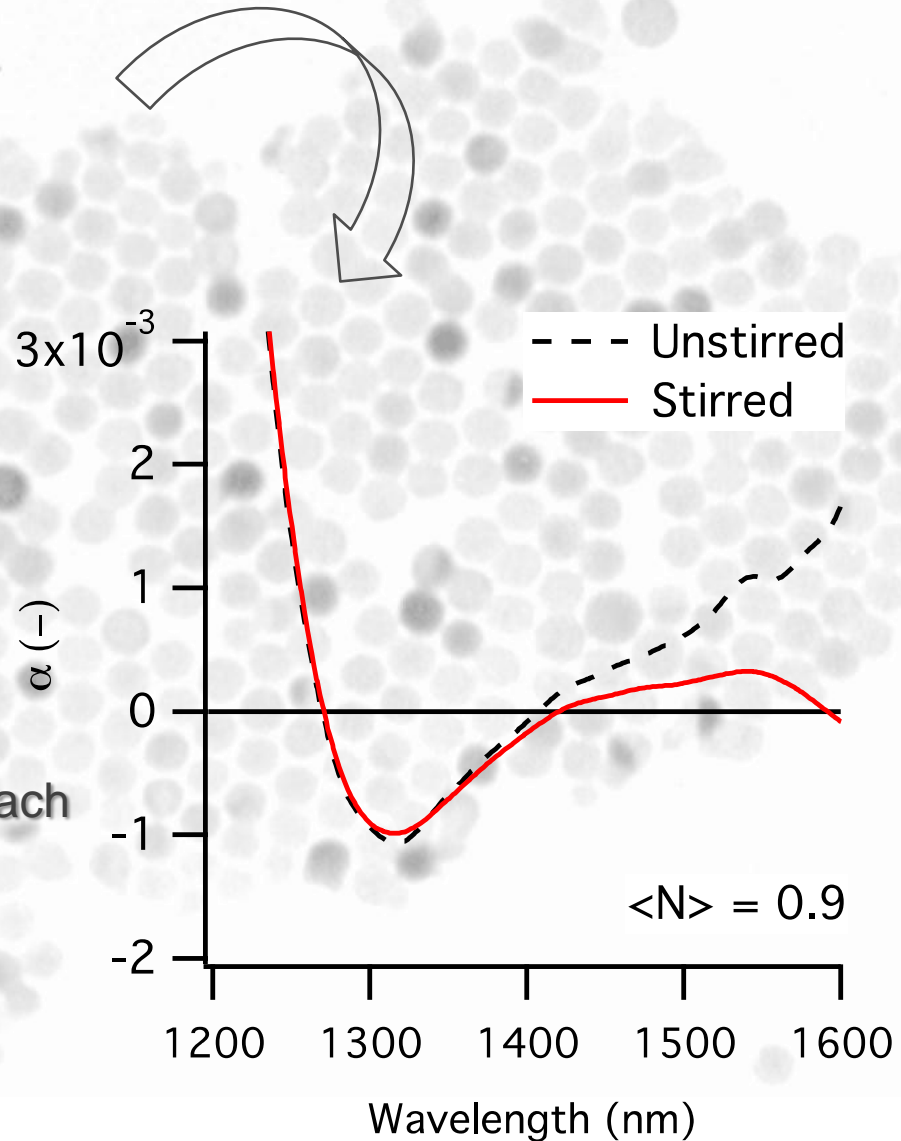


**Gain is due to single excitons !**

# To stir or not to stir ...



Stirring has no influence on bleach  
but reduces PA background !



# HgTe, really that great ?

Lowest gain threshold ever reported for colloidal NC, in essence thresholdless.

Long gain lifetime (up to radiative lifetime of 40 ns)



Low threshold/Long Gain lifetime = 5 orders of magnitude lower threshold than current NIR colloidal materials (PbS, PbSe, ...)

**And :**

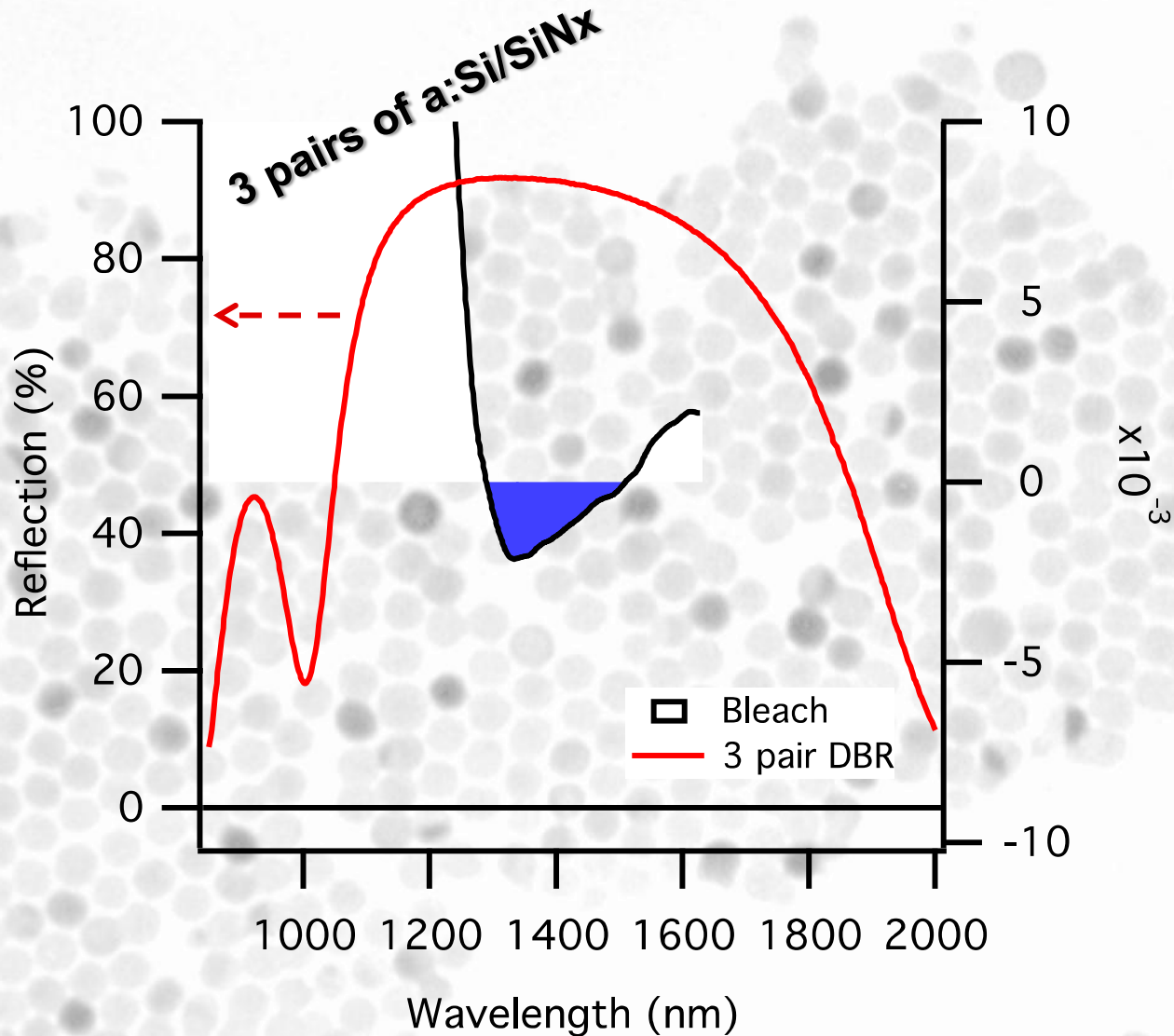
Gain is broadband (>200 nm) and achieved throughout the entire OESCL band

Easy wet chemical synthesis, no vacuum techniques needed

# To conclude

- Inorganic dye, stable under long laser exposure
- Stable under ambient, not air-sensitive
- Easy synthesis (1 minute) at low T (60° C)
- Gain over the entire OESCL band

# DBR fabrication – a:Si/SiNx



# Acknowledgements

